Discrete POWER & Signal **Technologies** 

# **MPS3703**

**MPS3703** 

FAIRCHILD

SEMICONDUCTOR IM



# **PNP General Purpose Amplifier**

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 500 mA. Sourced from Process 63. See PN2907A for characteristics.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>CBO</sub>	Collector-Base Voltage	50	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
Ic	Collector Current - Continuous	800	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# Thermal Characteristics

Thermal Characteristics     TA = 25°C unless otherwise noted					
Symbol	Characteristic	Max	Units		
		MPS3703			
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C		
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W		
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	200	°C/W		

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# PNP General Purpose Amplifier (continued)

Electrical Characteristics TA = 25°C unless otherwise noted					
Symbol	Parameter	Test Conditions	Min	Max	Units

# OFF CHARACTERISTICS

V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	30		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu A, I_{\rm E} = 0$	50		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{E} = 100 \ \mu A, I_{C} = 0$	5.0		V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 20 V, I_E = 0$		100	nA
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_{C} = 0$		100	nA

## **ON CHARACTERISTICS\***

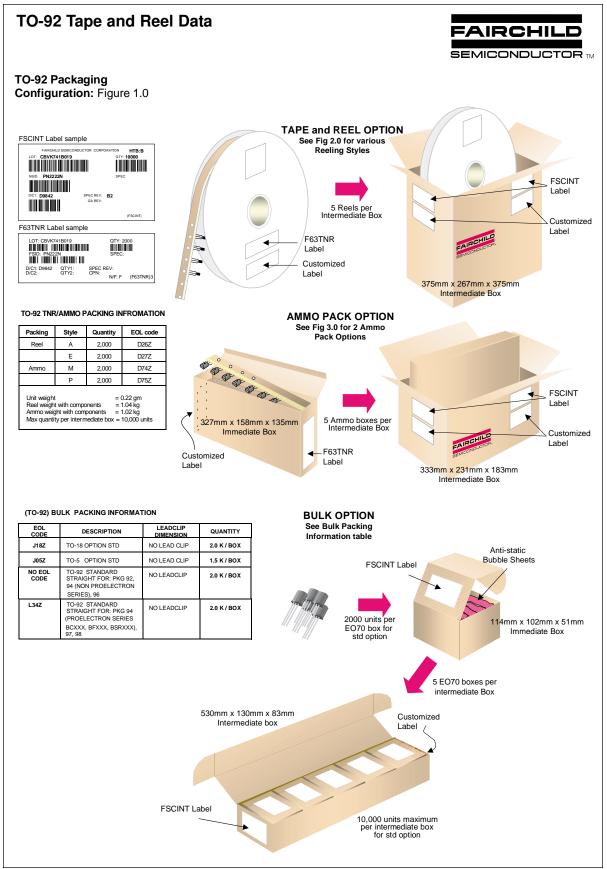
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 50 \text{ mA}$	30	150	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_{\rm C} = 50$ mA, $I_{\rm B} = 5.0$ mA		0.25	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$I_{\rm C}$ = 50 mA, $V_{\rm CE}$ = 5.0 V	0.6	1.0	V

# SMALL SIGNAL CHARACTERISTICS

Cob	Output Capacitance	V <sub>CB</sub> = 10 V, f = 1.0 MHz		12	pF
f <sub>T</sub>	Current Gain - Bandwidth Product	$I_{C} = 50 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 20 MHz	100		MHz

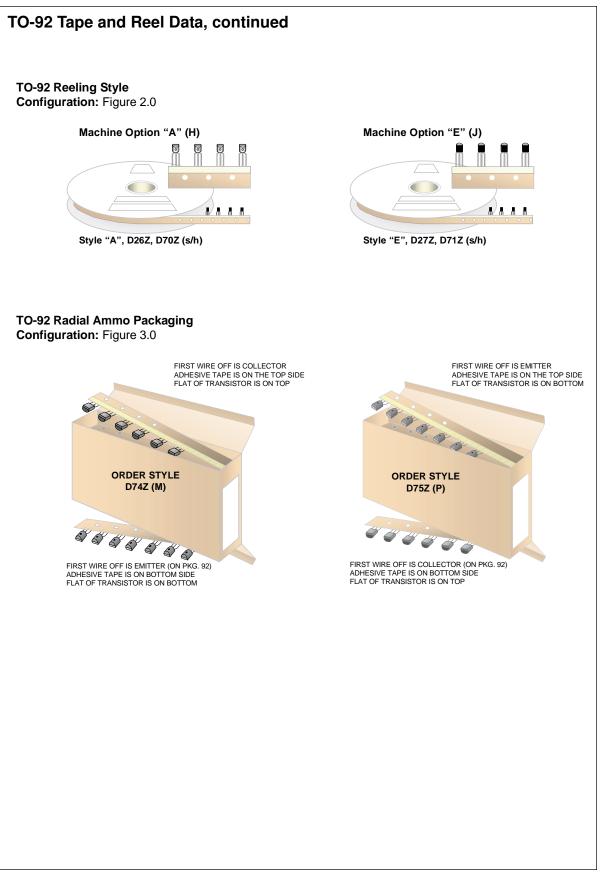
\*Pulse Test: Pulse Width $\leq$  300 µs, Duty Cycle $\leq$  2.0%

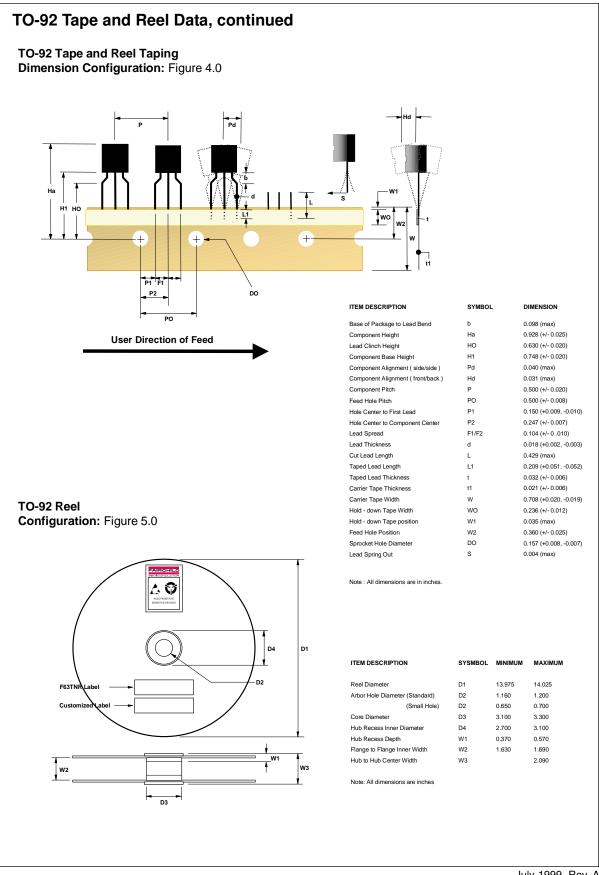
# MPS3703



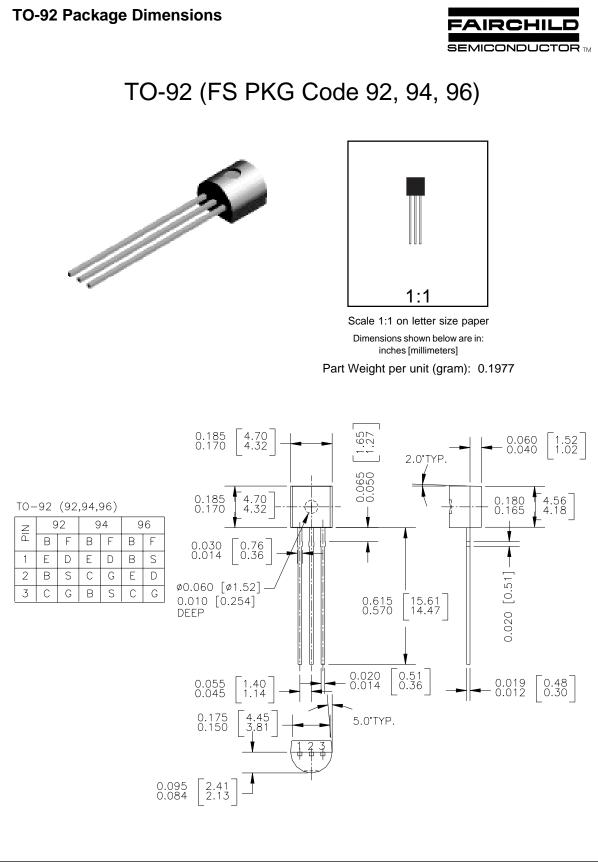
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Datasheet Identification	Product Status	Definition
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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